74HC2G02-Q100; 74HCT2G02-Q100

Dual 2-input NOR gate Rev. 1 — 11 November 2013

Product data sheet

General description 1.

The 74HC2G02-Q100; 74HCT2G02-Q100 is a dual 2-input NOR gate. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

Features and benefits 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
 - For 74HC2G02-Q100: CMOS level
 - ◆ For 74HCT2G02-Q100: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ♦ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)



3. Ordering information

Table 1. Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74HC2G02DP-Q100	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8	SOT505-2						
74HCT2G02DP-Q100			leads; body width 3 mm; lead length 0.5 mm							
74HC2G02DC-Q100	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package;	SOT765-1						
74HCT2G02DC-Q100			8 leads; body width 2.3 mm							

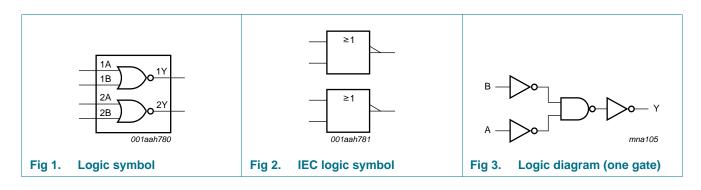
4. Marking

Table 2. Marking code

Type number	Marking code [1]
74HC2G02DP-Q100	H02
74HCT2G02DP-Q100	T02
74HC2G02DC-Q100	H02
74HCT2G02DC-Q100	T02

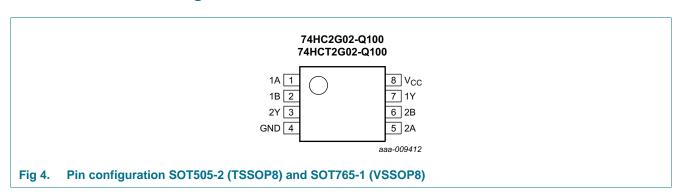
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input	Output	
nA	nB	nY
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

^[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
I _O	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	<u>[1]</u> _	25	mA
I _{CC}	supply current		<u>[1]</u> _	50	mA
I_{GND}	ground current		<u>[1]</u> –50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P_D	dynamic power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	300	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74H	C2G02-0	100	74H0	Unit		
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	-40	°C to +8	85 °C	-40 °C 1	Unit		
			Min	Typ[1]	Max	Min	Max	
74HC2G0	2-Q100							
V_{IH}	HIGH-level input	$V_{CC} = 2.0 \text{ V}$	1.5	1.2	-	1.5	-	V
	voltage	$V_{CC} = 4.5 \text{ V}$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	V
V _{IL}	LOW-level input	$V_{CC} = 2.0 \text{ V}$	-	0.8	0.5	-	0.5	V
	voltage	$V_{CC} = 4.5 \text{ V}$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	V

74HC_HCT2G02_Q100

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^[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

Table 7. Static characteristics ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	-40 °C	to +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}				ı		
	voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_O = -20 \mu A$; $V_{CC} = 6.0 \text{ V}$	5.9	6.0	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current	per input pin; $V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	10	-	20	μΑ
Cı	input capacitance		-	1.5	-	-	-	рF
74HCT2G	02-Q100							
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	0.8	-	0.8	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
ı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±1.0	-	±1.0	μΑ
CC	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ
Δl _{CC}	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_{I} = V_{CC} - 2.1 \text{ V}; I_{O} = 0 \text{ A}$	-	-	375	-	410	μΑ
C _I	input capacitance		-	1.5	-	-	-	рF

^[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6.

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	-40 °C t	to +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
74HC2G	02-Q100								
t _{pd}	propagation delay	nA and nB to nY; see Figure 5	[2]						
		V _{CC} = 2.0 V		-	26	95	-	110	ns
		V _{CC} = 4.5 V		-	9	19	-	22	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	9	-	-	-	ns
		V _{CC} = 6.0 V		-	8	16	-	20	ns
t _t	transition time	see Figure 5	[3]						
		V _{CC} = 2.0 V		-	19	95	-	125	ns
		V _{CC} = 4.5 V		-	7	19	-	25	ns
		V _{CC} = 6.0 V		-	5	16	-	20	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$	[4]	-	10	-	-	-	pF
74HCT2	G02-Q100								
t _{pd}	propagation delay	nA and nB to nY; see Figure 5	[2]						
		V _{CC} = 4.5 V		-	12	24	-	29	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	12	-	-	-	ns
t _t	transition time	$V_{CC} = 4.5 \text{ V}$; see Figure 5	[3]	-	6	19	-	22	ns
C _{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	<u>[4]</u>	-	10	-	-	-	pF

^[1] All typical values are measured at $T_{amb} = 25$ °C.

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o)$$
 where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

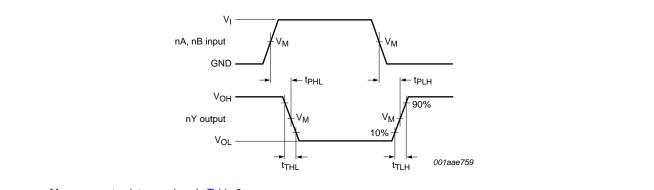
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

^[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

^[3] t_t is the same as t_{TLH} and t_{THL} .

^[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

12. Waveforms



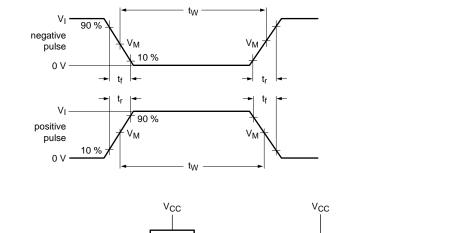
Measurement points are given in Table 9.

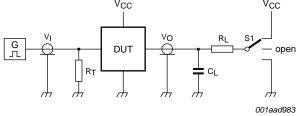
 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are typical output voltage levels that occur with the output load.

Fig 5. Propagation delay data input (nA, nB) to data output (nY) and transition time output (nY)

Table 9. Measurement points

Туре	Input	Output
	V _M	V _M
74HC2G02-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT2G02-Q100	1.3 V	1.3 V





Test data is given in Table 10.

Definitions for test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

 R_1 = Load resistance.

S1 = Test selection switch.

Fig 6. Test circuit for measuring switching times

Table 10. Test data

Туре	Input		Load	S1 position	
	VI	t _r , t _f	CL	R _L	t _{PHL} , t _{PLH}
74HC2G02-Q100	GND to V _{CC}	≤ 6 ns	15 pF, 50 pF	1 kΩ	open
74HCT2G02-Q100	GND to 3 V	≤ 6 ns	15 pF, 50 pF	1 kΩ	open

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

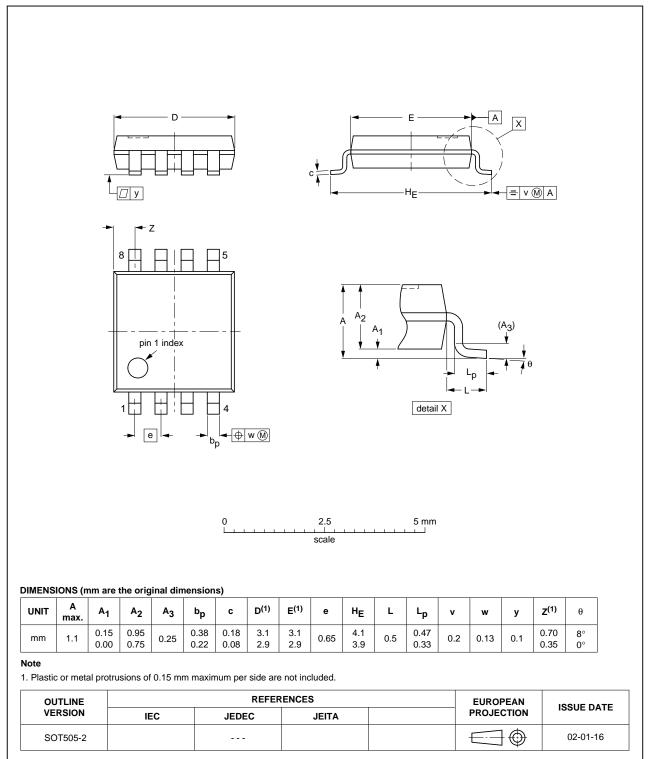


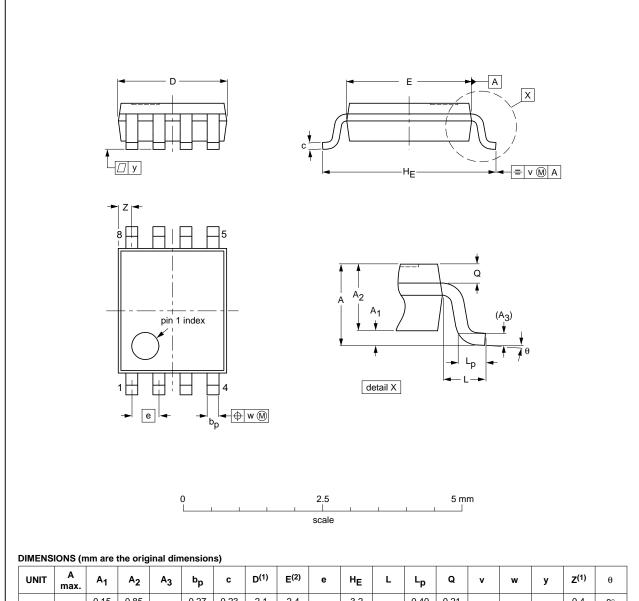
Fig 7. Package outline SOT505-2 (TSSOP8)

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VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	Α3	bp	C	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT765-1		MO-187				02-06-07

Package outline SOT765-1 (VSSOP8)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description	
CMOS	Complementary Metal Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G02_Q100 v.1	20131111	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Dual 2-input NOR gate

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